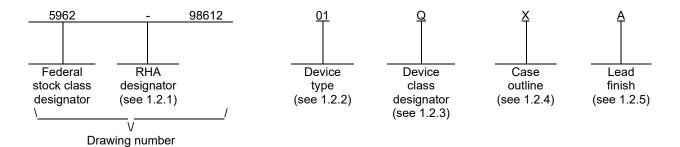
	REVISIONS								
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED						
Α	Changes IAW NOR 5962-R065-99 TVN	99-06-03	Monica L. Poelking						
В	Update boilerplate to MIL-PRF-38535 requirements. Incorporate Revision A changes from NOR 5962-R065-99 CFS	03-03-18	Thomas M. Hess						
С	Update boilerplate to current MIL-PRF-38535 requirements CFS	07-12-12	Thomas M. Hess						
D	Add device type 02 PHN	10-08-11	Thomas M. Hess						
E	Update boilerplate to current MIL-PRF-38535 requirements PHN	18-09-11	Thomas M. Hess						
F	Update device type 02 availability to bulletin page. Update boilerplate to MIL-PRF-38535 requirements DRH	24-05-08	Muhammad A. Akbar						



REV	F	F	F	F	F	F	F	F	F	F	F	F								
SHEET	35	36	37	38	39	40	41	42	43	44	45	46								
REV	F	F	F	F	F	F	F	F	F	F	F	F	F	F	F	F	F	F	F	F
SHEET	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34
REV STATUS		REV	,		F	F	F	F	F	F	F	F	F	F	F	F	F	F		
OF SHEETS				SHE	EΤ		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A				PREI	PARED T		. Nguye	en		DLA LAND AND MARITIME										
STANDARD MICROCIRCUIT				CHE	CKED E		. Nguye	en		COLUMBUS, OHIO 43218-3990 https://www.dla.mil/LandandMaritime										
DRA				APPI	ROVED Mo		. Poelki	ng		MICROCIRCUIT, DIGITAL, CMOS, DIGITAL SIGNAL										
THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS		BLE	DRA	WING A		VAL D	ATE		PROCESSOR CONTROLLER, MONOLITHIC SIL											
	AND AGENCIES OF THE DEPARTMENT OF DEFENSE		_	REVI	SION L	.EVEL				SIZE			CODE			59	962-9	9861	12	
ΔMS	SC N/A					ı	=			Α	1	6	7268							
Aivic	JO 14/74									SHEI	ΕT	1	OI	=	46					

1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents two product assurance class levels consisting of high reliability (device classes Q) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.
 - 1.2 PIN. The PIN is as shown in the following example:



- 1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 <u>Device type(s)</u>. The device type(s) identify the circuit function as follows:

Device type	Generic number	Operating temperature range	Circuit function
01	320F240	-55°C to +125°C	Digital signal processor controller
02	320F240	-55°C to +115°C	Digital signal processor controller

1.2.3 <u>Device class designator</u>. The device class designator is a single letter identifying the product assurance level as follows:

Device class

Device requirements documentation

Q or V

Certification and qualification to MIL-PRF-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
X	See figure 1	132	Ceramic guad flatpack

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

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1.3 Absolute maximum ratings. 1/	
Supply voltage range (V_{DD})	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$
1.4 Recommended operating conditions.	2.37 G/W
Digital supply voltage range (DV _{DD}) Supply voltage return	
High level input voltage range (V _{IH}): XTAL1/CLKIN	
PORESET , NMI, RS , and TRST All other inputs Low level input voltage range (V _{IL}):	
XTAL1/CLKINAll other input surrent (I _{OH}): High level output current (I _{OH}):	
RSIOPA[0:3], SCIRXD/IO, SCITXD/IO, XINT2/IO, XINT3/IOPB6, TMRCLK/IOPB	3/IO,
EMU0, EMU1/OFF All other outputsLow level output current (I _{OL}):	16 mA <u>3</u> /
IOPA[0:3], SCIRXD/IO, SCITXD/IO, XINT2/IO, XINT3/IOPB6, TMRCLK/IOPB	3/IO,
EMU0, EMU1/OFF All other outputs Case operating temperature range (Tc):	7.5 mA <u>3</u> /
Device type 01	55°C to +115°C
Recommended operating conditions for 10-bit dual ana Analog supply voltage range (V _{CCA})Analog ground (V _{SSA})Analog supply reference source range (V _{REFHI})Analog ground reference source range (V _{REFLO})Analog input voltage range – ADCIN0-ADCIN15 (V _{AI})	log-to-digital converter (ADC):
· · · · · ·	

Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

 $[\]underline{4}$ / V_{REFHI} and V_{REFLO} must be stable, within $\pm 1/2$ LSB of the required resolution, during the entire conversion time.

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V_{DD} refers to supply voltage types CV_{DD} (digital core supply voltage), DV_{DD} (digital I/O supply voltage), and V_{DDP} (programming voltage supply). All voltages are measured with respect to $V_{\rm SS}$. Typical readings derived from Spice simulations. Not production tested.

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.

MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at https://quicksearch.dla.mil/.)

2.2 <u>Non-Government publications</u>. The following document(s) form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these document(s) are those cited in the solicitation or contract.

INSTITUTE OF ELECTRICAL AND ELECTRONICS ENGINEERS (IEEE)

IEEE Standard 1149.1 - IEEE Standard Test Access Port and Boundary Scan Architecture.

(Copies of these documents are available online at https://www.ieee.org/.)

2.3 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.
 - 3.2.1 Case outline. The case outline shall be in accordance with 1.2.4 herein and on figure 1.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.
 - 3.2.3 <u>Block diagram</u>. The block diagram shall be as specified on figure 3.
 - 3.2.4 Boundary scan instruction codes. The boundary scan instruction codes shall be as specified on figure 4.
 - 3.2.5 Test circuit and timing waveforms. The test circuit and timing waveforms are as specified on figure 5.

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- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.
- 3.6 <u>Certificate of compliance</u>. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime -VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.
 - 3.8 IEEE 1149.1 compliance. These devices shall be compliant to IEEE 1149.1.

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		TABLE I. Elec	ctrical performance chara	cteristics.				
Test	Symbol	$+4.5 \text{ V} \le$ $-55^{\circ}\text{C} \le \text{T}_{\text{C}} \le +12$ $-55^{\circ}\text{C} \le \text{T}_{\text{C}} \le +11$	conditions ≤ V _{DD} ≤ +5.5 V 25°C for device type 01 5°C for device type 02 erwise specified	Device types	Group A subgroups	Lim Min	Max	Unit
High-level output voltage	V _{OH}	I _{OH} = MAX		All	1, 2, 3	2.4		V
Low-level output voltage	V _{OL}	I _{OL} = MAX		All	1, 2, 3		0.6	V
Input current	Iı	$V_I = V_{SS}$ or V_{DD}	TRST with internal pulldown	All	1, 2, 3	-10	500	μА
			EMU0, EMU1/OFF , TMS, TCK, and TDI, with internal pullup			-500	10	
			All other input pins			-10	10	
Output current, high impedance state (off-state)	loz	$V_O = V_{DD}$ or 0.0 V		All	1, 2, 3	-5	5	μА
Supply current, operating mode	I _{DD1}	$t_{c(CO)}$ = 50 ns		All	1, 2, 3		100 <u>1</u> /	mA
Supply current, idle 1 low-power mode	I _{DD2}	$t_{c(CO)}$ = 50 ns		All	1, 2, 3		50 <u>1</u> /	mA
Supply current, idle 2 low-power mode	Іррз	$t_{c(CO)}$ = 50 ns		All	1, 2, 3		7 <u>1</u> /	mA
Supply current, PLL power-down mode	I _{DD4}	$t_{c(CO)}$ = 50 ns		All	1, 2, 3		5 <u>1</u> /	mA
Supply current, OSC power-down mode	I _{DD5}	$t_{c(CO)} = 50 \text{ ns}$		All	1, 2, 3		400 <u>1</u> /	μА
Flash programming supply current	I _{DDP}	$t_{c(CO)} = 50 \text{ ns}$		All	1, 2, 3		10 <u>1</u> /	mA
Input capacitance	Cı	See 4.4.1c		All	4		15	pF
Output capacitance	Co	See 4.4.1c		All	4		15	pF
Functional testing		See 4.4.1b		All	7, 8			

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-	IAL	BLE I. <u>Electrica</u>	al performano	<u>e characteristic</u>	<u>s</u> - Conti	nued.			
Test	Symbol	+4.5 -55°C ≤ T _C ≤			Device types	Group A subgroups	Limi Min	Max	Unit
			s otherwise sp						
Clock options - Input clo	ock frequenc	y with the PLL	circuit disable	ed	,				
Input clock frequency, divide-by-2 mode	f _{x1}				All	9, 10, 11	0 <u>2</u> /	40	MHz
Input clock frequency, divide-by-1 mode	f _{x2}				All	9, 10, 11	0 <u>2</u> /	20	
Clock options - Switchin	ıg character	istics, H = 0.5 t	c(CO) <u>3</u> /						
Cycle time, CPUCLK	$t_{\text{c}(\text{CPU})}$	See figure 5	CLKIN divid	e by 2	All	9, 10, 11	2t _{c(CI)} <u>1</u> /	<u>2</u> /	ns
			CLKIN divid	e by 1			t _{c(CI)} 1/		
Cycle time, SYSCLK	$t_{\text{c}(\text{SYS})}$	See figure 5	CPUCLK div	vide by 2	All	9, 10, 11	2t _{c(CPU)} <u>1</u> /	<u>2</u> /	ns
			CPUCLK div	vide by 4 <u>4</u> /			4t _{c(CPU)} <u>1</u> /		
Cycle time, CLKOUT	$t_{\text{c(CO)}}$	See figure 5	CLKIN divid	e by 2	All	9, 10, 11	2t _{c(CI)} <u>1</u> /	<u>2</u> /	ns
			CLKIN divid	e by 1			t _{c(CI)}	<u>2</u> /	
Delay time, XTAL1/CLKIN high to CLKOUT high/low	t _{d(CIH-CO)}	See figure 5			All	9, 10, 11	3	22	ns
Fall time, CLKOUT	$t_{f(CO)}$	1			All	9, 10, 11		5 <u>1</u> /	ns
Rise time, CLKOUT	t _{r(CO)}				All	9, 10, 11		5 <u>1</u> /	ns
Pulse duration, CLKOUT low	$t_{w(COL)}$				All	9, 10, 11	H-10	H-1	ns
Pulse duration, CLKOUT high	$t_{\text{w(COH)}}$				All	9, 10, 11	H+0	H+8	ns
Clock options - Timing r	equirement	s							
Cycle time,	t _{c(CI)}	See figure 5	Divide by 2		All	9, 10, 11	25	<u>2</u> /	ns
XTAL1/CLKIN			Divide by 1]		50	<u>2</u> /	
Fall time, XTAL1/CLKIN	$t_{f(CI)}$	See figure 5			All	9, 10, 11		5 <u>1</u> /	ns
Rise time, XTAL1/CLKIN	t _{r(CI)}				All	9, 10, 11		5 <u>1</u> /	ns
Pulse duration, XTAL1/CLKIN low as a percentage of t _{c(CI)}	tw(CIL)				All	9, 10, 11	45	55	%
Pulse duration, XTAL1/CLKIN high as a percentage of t _{c(Cl)}	tw(CIH)				All	9, 10, 11	45	55	%
See footnotes at end of ta	able.				ı	1		1	I
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Test	Symbol		Test conditio		Device	Group A	Lin	nits	Unit
	,	+4.5 -55°C ≤ T _C ≤ -55°C ≤ T _C ≤	5 V ≤ V _{DD} ≤ + ≤ +125°C for	-5.5 V device type 01 device type 02	types	subgroups	Min	Max	
Clock options - Input ch	naracteristics	with the PLL cire	cuit enabled						
Input clock frequency	f _x	External refer	ence crystal	= 4 MHz	All	9, 10, 11		4 <u>1</u> /	MHz
		External refer			_			6 <u>1</u> /	
		External refer	ence crystal	= 8 MHz				8 <u>1</u> /	
Load capacitance	C1, C2				All	4		10 <u>1</u> /	pF
Clock options - Switchin	ng characteri	1	CO)		1		1	1	_
Cycle time, CPUCLK	$t_{c(CPU)}$	See figure 5	Before PLI CLKIN di		All	9, 10, 11	2t _{c(CI)} <u>1</u> /	<u>2</u> /	ns
			Before PLI CLKIN di				t _{c(CI)} <u>1</u> /		
			After PLL	lock			50 <u>1</u> /		
Cycle time, SYSCLK	t _{c(SYS)}	See figure 5	CPUCLK (divide by 2	All	9, 10, 11	2t _{c(CPU)} <u>1</u> /	<u>2</u> /	ns
			CPUCLK of	divide by 4			4t _{c(CPU)}		
Cycle time, CLKOUT	t _{c(CO)}	See figure 5	L		All	9, 10, 11	50	<u>2</u> /	ns
Fall time, CLKOUT	t _{f(CO)}	1			All	9, 10, 11		5 <u>1</u> /	ns
Rise time, CLKOUT	t _{r(CO)}	1			All	9, 10, 11		5 <u>1</u> /	ns
Pulse duration, CLKOUT low	t _{w(COL)}				All	9, 10, 11	H-10	H-1	ns
Pulse duration, CLKOUT high	t _{w(COH)}				All	9, 10, 11	H+0	H+8	ns
Transition time, PLL synchronized after	tp	See figure 5	Before PLI CLKIN di		All	9, 10, 11		2000 t _{c(CI)}	ns
PLL enabled			Before PLI CLKIN di		-			1000 t _{c(CI)}	
Clock options - Timing	requirements	<u>3</u> /	•					•	
Cycle time, XTAL1/CLKIN	t _{c(CI)}	See figure 5	External re		All	9, 10, 11	250	<u>2</u> /	ns
			External re				167		
			External re				125		
Fall time, XTAL1/CLKIN	t _{f(CI)}	See figure 5	ı		All	9, 10, 11		5 <u>1</u> /	ns
Rise time, XTAL1/CLKIN	t _{r(CI)}				All	9, 10, 11		5 <u>1</u> /	ns
See footnotes at end of t	able.	•					•		•
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	TABLE	I. <u>Electrical p</u>	erformanc	e characteristics -	Continue	d.			
Test	Symbol		Test cond	itions	Device	Group A	L	imits	Unit
	,	+4. -55°C ≤ Tc ≤ -55°C ≤ Tc ≤	5 V ≤ V _{DD} ≤ +125°C 1 ≤ +115°C 1		types	subgroups	Min	Max	
Clock options - Timing re	equirements -	Continued 3	<u>3</u> /						
Pulse duration, XTAL1/CLKIN low as a percentage of t _{c(Cl)}	t _{w(CIL)}	See figure 5			All	9, 10, 11	40	60	%
Pulse duration, XTAL1/CLKIN high as a percentage of t _{c(CI)}	t _{w(CIH)}				All	9, 10, 11	40	60	%
Low-power mode timings	 Switching ch 	naracteristics, F	H = 0.5 t _{c(C)}	(O)				•	•
Delay time, CLKOUT switching to program execution resume 3/	t _{d(WAKE-A)}	See figure 5	Idle 1 an	d idle 2	All	9, 10, 11		15xt _{c(CO)} <u>1</u> / 15xt _{c(CI)}	ns
Delay time, idle instruction executed	t _{d(IDLE-COH)}	See figure 5	down, (LL power DSC power	All	9, 10, 11		<u>1</u> / 500 <u>1</u> /	ns
to CLKOUT high 3/ Delay time, CLKOUT switching to PLL synchronized 3/	td(WAKE-LOCK)	See figure 5	PLL or C down	OSC power	All	9, 10, 11		100 <u>1</u> /	μs
Delay time, wakeup interrupt asserted to oscillator running	t _{d(WAKE-OSC)}	See figure 5	OSC pov	wer down	All	9, 10, 11		10 <u>1</u> /	ms
Delay time, idle instruction executed to oscillator power off	t _d (IDLE-OSC)	See figure 5	OSC pov	wer down	All	9, 10, 11		60 <u>1</u> /	μS
Memory and parallel I/O ir	nterface read ti	mings – Switc	ching char	acteristics for a me	emory read	I, H = 0.5 t _{c(0}	co) <u>5</u> /	1	
Delay time, CLKOUT/IOPC1 low to address valid	t _{d(CO-A)RD}	See figure 5			All	9, 10, 11		17	ns
Delay time, CLKOUT/IOPC1 low to STRB low	t _{d(CO-SL)RD}				All	9, 10, 11		10	ns
Delay time, CLKOUT/IOPC1 low to STRB high	t _{d(CO-SH)} RD				All	9, 10, 11		6	ns
Delay time, CLKOUT/ IOPC1 low to PS, DS, IS, and BR low	t _{d(CO-ACTL)} RD				All	9, 10, 11		10	ns
Delay time, CLKOUT/ IOPC1 low to PS, DS, IS, and BR high	td(co-acth)rd				All	9, 10, 11		10	ns
See footnotes at end of ta	ıble.	1			1	1		1	
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	TABLE I	. Electrical perf	ormance characteristics -	- Continu	ed.			
Test	Symbol		est conditions	Device	Group A	Lir	nits	Unit
		-55 °C \leq T _C \leq + -55 °C \leq T _C \leq +	$V \le V_{DD} \le +5.5 \text{ V}$ 125°C for device type 01 115°C for device type 02 otherwise specified	types	subgroups	Min	Max	
Memory and parallel I/O in	terface read tim	nings – Timing	requirements for a memor	ry read, H	= 0.5 t _{c(CO)}	<u>5</u> /	•	
Access time, from address valid to read	t _{a(A)} <u>1</u> /	See figure 5	0 wait state	All	9, 10, 11		2H-32	ns
data ———————————————————————————————————			1 wait state				4H-32	
Setup time, data read before CLKOUT/IOPC1 low	t _{su(D-COL)RD}	See figure 5		All	9, 10, 11	13		ns
Hold time, data read after CLKOUT/IOPC1 low	t _{h(COL-D)RD}			All	9, 10, 11	2		ns
Memory and parallel I/O in	L terface write tim	ı nings – Switchiı	ng characteristic for a me	Mory write	e, H = 0.5 t _{c(0}	co) 5/		
Delay time, CLKOUT/IOPC1 high to address valid	t _{d(CO-A)W}	See figure 5		All	9, 10, 11	, _	17	ns
Delay time, CLKOUT/IOPC1 low to data bus driven	t _{d(CO-D)}			All	9, 10, 11		15	ns
Delay time, address valid after WE high	t _{d(D-WH)}			All	9, 10, 11	H-8		ns
Pulse duration, WE high	t _{w(WH)}			All	9, 10, 11	2H-11		ns
Pulse duration, WE low	t _{w(WL)}			All	9, 10, 11	2H-11		ns
Delay time, CLKOUT/IOPC1 low to WE low	t _{d(CO-WL)}			All	9, 10, 11		9	ns
Delay time, CLKOUT/IOPC1 low to WE high	t _{d(CO-WH)}			All	9, 10, 11		9	ns
Delay time, write data valid before WE high	t _{d(WH-D)}			All	9, 10, 11	2H-8		ns
Delay time, WE high to data bus high-Z	t _{d(D-WHZ)}			All	9, 10, 11	0	5	ns
Delay time, CLKOUT/IOPC1 low to STRB low	t _{d(CO-SL)} W			All	9, 10, 11		10	ns
See footnotes at end of tal	ole.							
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	TABLE I	l. Electrical performanc	e characteristics -	Continu	ed.			
Test	Symbol	Test cond		Device	Group A	Lin	nits	Unit
		$\begin{array}{c} +4.5 \text{ V} \leq \text{V}_{DD} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +125^{\circ}\text{C} \uparrow \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +115^{\circ}\text{C} \uparrow \\ \text{unless otherwis} \end{array}$	for device type 01 for device type 02	types	subgroups	Min	Max	
Memory and parallel I/O int	erface write tin	nings – Switching char	acteristic for a mer	nory write	e, H = 0.5 t _{c(C}	co) – Cor	ntinued	<u>5</u> /
Delay time, CLKOUT/IOPC1 low to STRB high	t _{d(CO-SH)} W	See figure 5		All	9, 10, 11		6	ns
Delay time, CLKOUT/ IOPC1 high to PS, DS, IS, and BR low	t _{d(CO-ACTL)} W			All	9, 10, 11		10	ns
Delay time, CLKOUT/ IOPC1 high to PS, DS, IS, and BR high	t _{d(CO-ACTH)} W			All	9, 10, 11		10	ns
Delay time, CLKOUT/IOPC1 high to R/\overline{W} low	t _{d(CO-RWL)}			All	9, 10, 11		10	ns
Delay time, CLKOUT/IOPC1 high to R/\overline{W} high	t _{d(CO-RWH)}			All	9, 10, 11		10	ns
READY timings - Timing	requirements	<u>6</u> /		ı	ı			
Setup time, READY low before CLKOUT/IOPC1 high	t _{su(R-CO)}	See figure 5		All	9, 10, 11	14		ns
Hold time, READY low after CLKOUT/IOPC1 high	t _{h(CO-R)}			All	9, 10, 11	0		ns
Valid time, READY after address valid on read	t _{v(R)} ARD <u>1</u> /			All	9, 10, 11		3H-31	ns
Valid time, READY after address valid on write	t _{v(R)AW} 1/			All	9, 10, 11		4H-31	ns
RS and PORESET timing	gs – Switching	characteristics for a re	set, H = 0.5 t _{c(CO)}					
Pulse duration, RS low 7/	t _{w(RSL1)} 1/	See figure 5		All	9, 10, 11	8t _{c(SYS)}		ns
Delay time, RS low to program address at reset vector	t _{d(RS)} <u>1</u> /			All	9, 10, 11	4H		ns
Delay time, RS high to reset vector executed	t _{d(EX)} <u>1</u> /			All	9, 10, 11	32H		ns
See footnotes at end of tal	ole.							
	ANDARD	MING	SIZE A			5	962-98	612
DLA LAN	D AND MARITI S, OHIO 43218	IME		REVISIO	ON LEVEL F	SH	IEET 11	

	TABLE	I. Electrical performanc	e characteristics -	Continue	ed.			
Test	Symbol	Test cond		Device	Group A	Lim	its	Unit
		$\begin{array}{c} +4.5 \text{ V} \leq \text{V}_{DD} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +125^{\circ}\text{C} \text{ 1} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +115^{\circ}\text{C} \text{ 1} \\ \text{unless otherwis} \end{array}$	for device type 01 for device type 02	types	subgroups	Min	Max	
RS and PORESET timing	gs – Timing re	quirements for a reset, l	$H = 0.5 t_{c(CO)}$					
Pulse duration, RS or PORESET low 8/	t _{w(RSL)} <u>1</u> /	See figure 5		All	9, 10, 11	5		ns
XF, BIO, and MP/MC time	ings – Switchii	ng characteristic, H = 0.9	5 t _{c(CO)}					
Delay time, CLKOUT high to XF high/low	t _{d(XF)}	See figure 5		All	9, 10, 11		11	ns
XF, BIO, and MP/MC time	ings – Timing	requirements, H = 0.5 t _c	(CO)					
Pulse duration, BIO low	t _{w(BIOL)}	See figure 5		All	9, 10, 11	2H+16		ns
Pulse duration, MP/MC valid 9/	tw(MPMCV) 1/			All	9, 10, 11	2H+24		ns
PWM/CMP timings - Swit	ching characte	ristic for PWM timing, H	= 0.5 t _{c(CO)}					
Delay time, CLKOUT high to PWM output switching	t _{d(PWM)} co <u>1</u> /	See figure 5		All	9, 10, 11		12	ns
PWM/CMP timings - Timi	ing requirement	ts		1	1			
Pulse duration, TMRDIR low/high	$t_{w(TMRDIR)}$ 1/	See figure 5		All	9, 10, 11	4H+12		ns
Pulse duration, TMRCLK low as a percentage of TMRCLK cycle time	tw(TMRCLKL) 1/			All	9, 10, 11	40	60	%
Pulse duration, TMRCLK high as a percentage of TMRCLK cycle time	tw(TMRCLKH) 1/			All	9, 10, 11	40	60	%
Cycle time, TMRCLK	t _{c(TMRCLK)} 1/			All	9, 10, 11	4xt _{c(CPU)}		ns
Capture and QEP timings	 Timing requi 	rements						
Pulse duration, CAP input low/high	t _{w(CAP)} <u>1</u> /	See figure 5		All	9, 10, 11	4H+12		ns
Interrupt timings - Switch	ing characterist	ics for interrupt, H = 0.5	t _{c(CO)}					
Delay time, PDPINT low to PWM to high-impedance state	t _{d(PWM)} PDP	See figure 5		All	9, 10, 11	0	15	ns
See footnotes at end of ta	ıble.							
	TANDARD	NATING.	SIZE A			59	62-98	612
DLA LAN	RCUIT DRA ND AND MARIT IS, OHIO 43218	IME		REVISIO	N LEVEL F	SHE	ET 12	

Test	Symbol	Т	est conditio	ons	Device	Group A	Lin	nits	Unit
	5 ,20.	+4.5 -55°C ≤ T _C ≤ ·	$V \le V_{DD} \le +$ +125°C for	+5.5 V device type 01 device type 02		subgroups	Min	Max	
Interrupt timings - Timing	requirement	S							
Pulse duration, INT input low/high	$t_{w(INT)}$	See figure 5			All	9, 10, 11	t _{c(SYS)} +12		ns
Pulse duration, PDPINT input low	$t_{w(PDP)}$				All	9, 10, 11	2H+18		ns
Delay time, INT low/high to interrupt-vector fetch	t _{d(INT)} <u>1</u> /				All	9, 10, 11	$\begin{array}{c} 2t_{c(SYS)} + \\ 4t_{c(CPU)} \end{array}$		ns
General-purpose input/out	put timings -	Switching cha	aracteristics	for a GPI/O, H	$= 0.5 t_{c(0)}$	CO)			
Delay time, CLKOUT low to GPO low/high	t _{d(GPO)} CO	See figure 5	XINT2/IO, IOPB6, IO and IOPO	OPB7,	All	9, 10, 11		33	ns
			All other G	SPOs .				25	
General-purpose input/out	put timings -	Timing require	ements						
Pulse duration, GPI high/low	t _{w(GPI)}	See figure 5			All	9, 10, 11	t _{c(SYS)} +12		ns
Serial communications inte	erface (SCI) I	/O timings – T	iming chara	acteristics for S	CI <u>10</u> /				
Cycle time, SCICLK	$t_{c(SCC)}$ <u>1</u> /	See figure 5	(BRR+1) is and BRR		All	9, 10, 11	16t _c	65536tc	ns
			(BRR+1) is and BRR				24t _c	65535tc	
Valid time, SCITXD data	t _{v(TXD)}	See figure 5	(BRR+1) is	2 = 0	All	9, 10, 11	t _{c(SCC)} -70	t _{c(SCC)} +70	ns
			(BRR+1) is and BRR				t _{c(SCC)} -70	t _{c(SCC)} +70	
Valid time, SCIRXD data	t _{v(RXD)}	See figure 5	(BRR+1) is and BRR		All	9, 10, 11	16t _c		ns
			(BRR+1) is and BRR				24t _c		
See footnotes at end of ta	able.								
	STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990			SIZE A				5962-986	612
DLA LAI					REV	ISION LEV	EL :	SHEET 13	

	TA	BLE I. Electric	cal performand	e characteris	stics - (Continued.			
Test	Symbol	+4.5 -55°C ≤ Tc ≤	Test conditions $V \le V_{DD} \le +5$. $+125^{\circ}C$ for de $+115^{\circ}C$ for de	vice type 01	Device types	Group A subgroups	Limi Min	its Max	Unit
		unless	otherwise spe	cified					
SPI master mode exte	rnal timing para	· ·	phase = 0) <u>^</u>	<u>l/ 11</u> /			ı	1	ı
Cycle time, SPICLK	t _{c(SPC)} M	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	4t _c <u>10</u> /	128t _c <u>10</u> /	ns
			(SPIBRR+1) or SPIBRR				5t _c <u>10</u> /	127t _c <u>10</u> /	
Pulse duration, SPICLK high	t _{w(SPCH)} м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 0)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -0 .5t _c -70	0.5t _{c(SPC)M} -0.5t _c	
Pulse duration, SPICLK low	t _{w(SPCL)M}	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 1)			(SPIBRR+1) or SPIBRR				$0.5t_{c(SPC)M}$ -0 $.5t_{c}$ -70	0.5t _{c(SPC)M} -0.5t _c	
Pulse duration, SPICLK low	t _{w(SPCL)M}	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 0)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} +0.5t _c -70	0.5t _{c(SPC)M} +0.5t _c	
Pulse duration, SPICLK high	t _{w(SPCH)} м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 1)	_		(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} +0.5t _c -70	0.5t _{c(SPC)M} +0.5t _c	
Delay time, SPICLK high	t _d (spcн-siмо)м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	-10	10	ns
(clock polarity = 0) to SPISIMO valid			(SPIBRR+1) or SPIBRR				-10	10	
Delay time, SPICLK low	t _{d(SPCL-SIMO)} м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	-10	10	ns
(clock polarity = 1) to SPISIMO valid			(SPIBRR+1) or SPIBRR				-10	10	
Hold time, SPISIMO data valid after	t _{h(SPCL-SIMO)М} <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	0.5t _{c(SPC)М} -7		ns
SPICLK low (clock polarity = 0)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} +0.5t _c -70		
Hold time, SPISIMO data valid after	t _{h(SPCH-SIMO)} м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR		All	9, 10, 11	0.5t _{c(SPC)M} -7		ns
SPICLK high (clock polarity = 1)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)М} +0.5t _c -70		
See footnotes at end	of table.								
MICD	STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990			SIZE A				5962-98	612
DLA					R	REVISION LE	EVEL	SHEET 14	

Test	Symbol		est conditions	Device	Group A	Limi	its	Uni
		$ \begin{array}{l} \textbf{-55}^{\circ}C \leq T_C \leq \\ \textbf{-55}^{\circ}C \leq T_C \leq \end{array} $	$V \le V_{DD} \le +5.5 \text{ V}$ +125°C for device type 01 +115°C for device type 02 otherwise specified	types	subgroups	Min	Max	
SPI master mode exte	rnal timing par	ameters (clock	phase = 0) - Continued	<u>1</u> / <u>11</u> /				
Setup time, SPISOMI before SPICLK	t _{su(SOMI-SPCL)M}	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0		ns
low (clock polarity = 0)			(SPIBRR+1) is odd or SPIBRR > 3			0		
Setup time, SPISOMI before SPICLK	t _{su(SOMI-SPCH)M}	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0		ns
high (clock polarity = 1)	<u></u>		(SPIBRR+1) is odd or SPIBRR > 3			0		
Hold time, SPISOMI data valid after	t _h (SPCL-SOMI)M 12/	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0.25t _{c(SPC)M} - 70		ns
SPICLK low (clock polarity = 0)	<u>.=</u>		(SPIBRR+1) is odd or SPIBRR > 3			0.5t _{c(SPC)M} -0 .5t _c -70		
Hold time, SPISOMI data valid after	t _{h(SPCH-SOMI)M} <u>12</u> /	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0.25t _{c(SPC)M} - 70		ns
SPICLK high (clock polarity = 1)			(SPIBRR+1) is odd or SPIBRR > 3			0.5t _{c(SPC)M} -0 .5t _c -70		
SPI master mode exte	rnal timing par	ameters (clock	phase = 1) <u>1</u> / <u>13</u> /					1
Cycle time, SPICLK	t _{c(SPC)M}	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	4t _c <u>10</u> /	128t _c <u>10</u> /	ns
			(SPIBRR+1) is odd or SPIBRR > 3			5t _c <u>10</u> /	127t _c <u>10</u> /	
Pulse duration, SPICLK high	t _{w(SPCH)М}	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 0)			(SPIBRR+1) is odd or SPIBRR > 3			0.5t _{c(SPC)M} -0 .5t _c -70	0.5t _{c(SPC)M} -0.5t _c	
Pulse duration, SPICLK low	t _{w(SPCL)M}	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 1)	12		(SPIBRR+1) is odd or SPIBRR > 3			0.5t _{c(SPC)M} -0 .5t _c -70	0.5t _{c(SPC)M} -0.5t _c	
Pulse duration, SPICLK low	t _{w(SPCL)M}	See figure 5	(SPIBRR+1) is even or SPIBRR = 0 or 2	All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 0)	12		(SPIBRR+1) is odd or SPIBRR > 3			0.5t _{c(SPC)M} +0.5t _c -70	0.5t _c (SPC)M +0.5t _c	
See footnotes at end	of table.							

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STANDARD

MICROCIRCUIT DRAWING
DLA LAND AND MARITIME

COLUMBUS, OHIO 43218-3990

	TA	BLE I. Electric	cal performanc	e characteris	stics - (Continued.			
Test	Symbol	+4.5 -55°C ≤ T _C ≤ -55°C ≤ T _C ≤	est conditions $V \le V_{DD} \le +5.4$ +125°C for de +115°C for de otherwise spe	vice type 01 vice type 02	Device types	Group A subgroups	Lim Min	its Max	Unit
SPI master mode exter	rnal timing para	ameters (clock	phase = 1) -	Continued	<u>1</u> / <u>13</u> /	•	•		
Pulse duration, SPICLK high	t _{w(SPCH)М}	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.5t _{c(SPC)M} -7	0.5t _{c(SPC)M}	ns
(clock polarity = 1)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} +0.5t _c -70	0.5t _{c(SPC)M} +0.5t _c	
Setup time, SPISIMO data valid before	t _{su(SIMO-SPCH)M}	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.5t _{c(SPC)M} -7		ns
SPICLK high (clock polarity = 0)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -7		
Setup time, SPISIMO data valid before	t _{su(SIMO-SPCL)M}	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.5t _{c(SPC)M} -7		ns
SPICLK low (clock polarity = 1)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -7		
Hold time, SPISIMO data valid after	t _h (spcн-siмо)м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.5t _{c(SPC)M} -7		ns
SPICLK high (clock polarity = 0)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -7		
Hold time, SPISIMO data valid after	th(SPCL-SIMO)M 12/	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.5t _{c(SPC)M} -7		ns
SPICLK low (clock polarity = 1)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -7		
Setup time, SPISOMI before SPICLK	t _{su(SOMI-SPCH)M}	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0		ns
high (clock polarity = 0)			(SPIBRR+1) or SPIBRR				0		
Setup time, SPISOMI before SPICLK	t _{su(SOMI-SPCL)M}	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0		ns
low (clock polarity = 1)			(SPIBRR+1) or SPIBRR				0		
Hold time, SPISOMI data valid after	t _h (spcн-soмі)м <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.25t _{c(SPC)M} - 70		ns
SPICLK high (clock polarity = 0)			(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -7		
Hold time, SPISOMI data valid after	t _{h(SPCL-SOMI)М} <u>12</u> /	See figure 5	(SPIBRR+1) or SPIBRR :		All	9, 10, 11	0.25t _{c(SPC)M} - 70		ns
SPICLK low (clock polarity = 1)	_		(SPIBRR+1) or SPIBRR				0.5t _{c(SPC)M} -7		
See footnotes at end	of table.								
MICO	STANDAR			SIZE A				5962-98	612
DLA	MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990				R	EVISION L		SHEET 16	

	TA	BLE I. <u>Electrical performanc</u>	e characteris	stics - (Continued.			
Test	Symbol	Test conditions $+4.5 \text{ V} \le \text{V}_{DD} \le +5.$		Device types	Group A subgroups	Lim Min	its Max	Unit
		$\label{eq:continuous} \begin{array}{l} -55^{\circ}C \leq T_{C} \leq +125^{\circ}C \text{ for de} \\ -55^{\circ}C \leq T_{C} \leq +115^{\circ}C \text{ for de} \\ \text{unless otherwise spe} \end{array}$	vice type 02			141111	Wax	
SPI slave mode extern	al timing requi	rements (clock phase = 0)	<u>1</u> / <u>14</u> /		•			
Cycle time, SPICLK	t _{c(SPC)} s	See figure 5		All	9, 10, 11	8t _c <u>10</u> /		ns
Pulse duration, SPICLK high (clock polarity = 0)	t _{w(SPCH)S} <u>12</u> /			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _{c(SPC)S}	ns
Pulse duration, SPICLK low (clock polarity = 1)	t _{w(SPCL)S} 12/			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _c (SPC)S	ns
Pulse duration, SPICLK low (clock polarity = 0)	t _{w(SPCL)S} 12/			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _{c(SPC)S}	ns
Pulse duration, SPICLK high (clock polarity = 1)	t _{w(SPCH)} s <u>12</u> /			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _c (SPC)S	ns
Delay time, SPICLK high (clock polarity = 0) to SPISOMI valid	t _d (spcн-somi)s <u>12</u> /			All	9, 10, 11	0.375t _{c(SPC)} s -70		ns
Delay time, SPICLK low (clock polarity = 1) to SPISOMI valid	t _d (SPCL-SOMI)S 12/			All	9, 10, 11	0.375t _{c(SPC)} s -70		ns
Valid time, SPISOMI data valid after SPICLK low (clock polarity = 0)	t _{v(SPCL-SOMI)S} 12/			All	9, 10, 11	0.75t _{c(SPC)S}		ns
Valid time, SPISOMI data valid after SPICLK high (clock polarity = 1)	t _{v(SPCH-SOMI)S} <u>12</u> /			All	9, 10, 11	0.75t _{c(SPC)S}		ns
Setup time, SPISIMO before SPICLK low (clock polarity = 0)	t _{su(SIMO-SPCL)} s			All	9, 10, 11	0		ns
Setup time, SPISIMO before SPICLK high (clock polarity = 1)	t _{su(SIMO-SPCH)} S <u>12</u> /			All	9, 10, 11	0		ns
See footnotes at end	of table.							
MICE	STANDAF OCIRCUIT I		SIZE A				5962-986	612
DLA	LAND AND M MBUS, OHIO	ARITIME		F	REVISION L	EVEL	SHEET 17	

	TA	BLE I. <u>Electrical performanc</u>	e characteristi	<u>cs</u> - Co	ontinued.			
Test	Symbol	Test conditions	 S	Device	Group A	Limi	ts	Unit
	,	$\begin{array}{c} +4.5 \text{ V} \leq \text{V}_{DD} \leq +5 \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +125^{\circ}\text{C for do} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +115^{\circ}\text{C for do} \\ \text{unless otherwise special} \end{array}$.5 V evice type 01 evice type 02		subgroups	Min	Max	
SPI slave mode extern	al timing requi	rements (clock phase = 0) –	Continued <u>1</u>	/ <u>14</u> /				
Valid time, SPISIMO data valid after SPICLK low (clock polarity = 0)	t _v (spcl-simo)s <u>12</u> /	See figure 5		All	9, 10, 11	0.5t _{c(SPC)} s		ns
Valid time, SPISIMO data valid after SPICLK high (clock polarity = 1)	t _{v(SPCH-SIMO)} s <u>12</u> /			All	9, 10, 11	0.5t _c (SPC)S		ns
SPI slave mode extern	nal timing requi	rements (clock phase = 1)	<u>1</u> / <u>15</u> /					
Cycle time, SPICLK	t _{c(SPC)} s	See figure 5		All	9, 10, 11	8t _c <u>10</u> /		ns
Pulse duration, SPICLK high (clock polarity = 0)	tw(spcн)s <u>12</u> /			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _{c(SPC)} s	ns
Pulse duration, SPICLK low (clock polarity = 1)	tw(SPCL)S <u>12</u> /			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _{c(SPC)} s	ns
Pulse duration, SPICLK low (clock polarity = 0)	t _{w(SPCL)} s <u>12</u> /			All	9, 10, 11	0.5t _{c(SPC)S} -7	0.5t _{c(SPC)} s	ns
Pulse duration, SPICLK high (clock polarity = 1)	t _{w(SPCH)} s <u>12</u> /			All	9, 10, 11	0.5t _{c(SPC)} s -7	0.5t _{c(SPC)} s	ns
Setup time, SPISOMI before SPICLK high (clock polarity = 0)	t _{su(SOMI-SPCH)S} <u>12</u> /			All	9, 10, 11	0.125tc(SPC)S		ns
Setup time, SPISOMI before SPICLK low (clock polarity = 1)	t _{su(SOMI-SPCL)} S <u>12</u> /			All	9, 10, 11	0.125tc(SPC)S		ns
Valid time, SPISOMI data valid after SPICLK high (clock polarity = 0)	t _{v(SPCH-SOMI)S} <u>12</u> /			All	9, 10, 11	0.75t _{c(SPC)S}		ns
Valid time, SPISOMI data valid after SPICLK low (clock polarity = 1)	t _{v(SPCL} -SOMI)S <u>12</u> /			All	9, 10, 11	0.75t _{c(SPC)} s		ns
See footnotes at end	of table.							
MODA	STANDAR		SIZE A				5962-986	612
DLA	DCIRCUIT D LAND AND MA MBUS, OHIO 4	ARITIME		RE	VISION LE F	VEL S	SHEET 18	

	TAE	BLE I. <u>Electrical per</u>	formanc	e characterist	<u>ics</u> - Co	ntinued.			
Test	Symbol		onditions		Device	Group A	Li	mits	Unit
		$ \begin{array}{c} +4.5 \text{ V} \leq \text{V}_{DD} \leq +5.5 \text{ V} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +125^{\circ}\text{C} \text{ for device type 01} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +115^{\circ}\text{C for device type 02} \\ \text{unless otherwise specified} \end{array} $			types	subgroups	Min	Max	
SPI slave mode extern	nal timing requi	rements (clock phas	se = 1) -	Continued	<u>1</u> / <u>15</u> /				
Setup time, SPISIMO before SPICLK high (clock polarity = 0)	t _{su(SIMO-SPCH)} S 12/	See figure 5			All	9, 10, 11	0		ns
Setup time, SPISIMO before SPICLK low (clock polarity = 1)	t _{su(SIMO-SPCL)S}	•			All	9, 10, 11	0		ns
Valid time, SPISIMO data valid after SPICLK high (clock polarity = 0)	t _{v(SPCH-SIMO)S} 12/				All	9, 10, 11	0.5t _{c(SPC})S	ns
Valid time, SPISIMO data valid after SPICLK low (clock polarity = 1)	t _{v(SPCL-SIMO)S} 12/	•			All	9, 10, 11	0.5t _{c(SPC})S	ns
10-bit dual analog-to-c	ligital converter	(ADC) – Electrica	l charact	eristics <u>16</u> /					
Analog supply	Icca	V _{CCA} = 5.5 V Converting		All	1, 2, 3		5	mA	
current			Non-cor	nverting				2	
		V _{CCA} = V _{REFHI} = 5.5 V	PLL or (power					1	
Input charge current, V _{REFHI} or V _{REFLO}	I _{ref}	V _{CCA} = V _{CCD} = V _{REF} V _{REFLO} = 0 V	ні = 5.5	V	All	1, 2, 3		5	mA
Analog input capacitance	Cai	Typical capacitive load on analog			All	4		6	pF
		input pin	Samplin	_					
Analog input source impedance	Z _{AI}	Analog input source for conversions to specifications			All	1, 2, 3		9	kΩ
Differential non- linearity error	E _{DNL}	Difference between step width and the			All	1, 2, 3	-1	1.5	LSB
Integral non- linearity error	EINL	Maximum deviation from the best straight line through the ADC transfer characteristics, excluding the quantization error			All	1, 2, 3		±1.5	LSB
Delay time, power- up to ADC valid	t _{d(PU)}	Time to stabilize analog stage after power-up			All	9, 10, 11		10	μS
See footnotes at end o	of table.								
MICEC	STANDAR			SIZE A				5962-98	8612
MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990					RE'	VISION LEVI F	ΞL	SHEET 19	

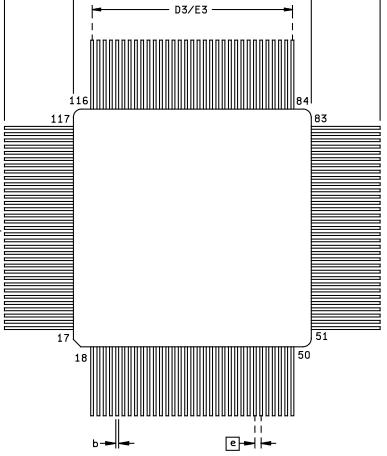
	TAB	SLE I. <u>Electrical performanc</u>	e characteristic	cs - Cor	tinued.			
Test	Symbol	$Test \ condition \\ +4.5 \ V \le V_{DD} \le + \\ -55^{\circ}C \le T_{C} \le +125^{\circ}C \ for \ c$ $-55^{\circ}C \le T_{C} \le +115^{\circ}C \ for \ c$ unless otherwise s	Device types	Group A subgroups	Lir Min	mits Max	Unit	
10-bit dual analog-to-di	<u>I</u> gital converter	(ADC) – Timing requirement	'					1
Cycle time, ADC prescaled clock	t _{c(AD)}	See figure 5	_	All	9, 10, 11	1		μs
Pulse duration, total sample/hold and conversion time <u>17</u> /	tw(SHC)			All	9, 10, 11	6.1		μs
Pulse duration, sample/hold time	t _{w(SH)}			All	9, 10, 11	t _{c(AD)}		μS
Setup time, analog input stable before sample/hold start	t _{su(SH)}			All	9, 10, 11	0		ns
Hold time, analog input stable after sample/hold complete	t _{h(SH)}			All	9, 10, 11	0		ns
Pulse duration, total conversion time	t _{w(C)}			All	9, 10, 11	4.5t _{c(AD)}		μs
Delay time, start of conversion to begin of sample and hold 18/	t _{d(SOC-SH)}			All	9, 10, 11	3t _{c(SYS)}		ns
Delay time, end of conversion to data loaded into result FIFO	t _{d(EOC-FIFO)}			All	9, 10, 11	3t _{c(SYS)}		ns
Flash EEPROM - Swi	tching charact	eristics		I				· ·
Program-erase endurance				All	9, 10, 11	10K		Cycle
Program pulse per word <u>19</u> /				All	9, 10, 11	1	150	Pulse
Erase pulses per array <u>19</u> /				All	9, 10, 11	1	1000	Pulses
Flash-write pulses per array <u>19</u> /				All	9, 10, 11	1	6000	Pulses
See footnotes at end o	f table.							
MICRO	STANDARI CIRCUIT DI	RAWING	SIZE A				5962-9	8612
DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990				REV	ISION LEVI F	EL	SHEET 20)

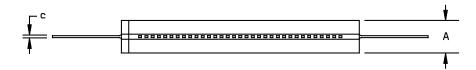
	TABL	E I. Electrical performanc	e characteristics	- Contin	ued.				
Test	Symbol	Test condition		Device	Group A		Limits	Unit	
		$ \begin{array}{c} +4.5 \text{ V} \leq \text{V}_{DD} \leq \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +125^{\circ}\text{C for} \\ -55^{\circ}\text{C} \leq \text{T}_{C} \leq +115^{\circ}\text{C for} \\ \text{unless otherwise} \end{array} $	device type 01 device type 02	types	subgroups	Min	Max		
Flash EEPROM - Timi	ing requirement	ts					•		
Delay time, after mode deselect to stabilization 19/	t _{d(BUSY)}			All	9, 10, 11	10		μS	
Delay time, verify read mode select to stabilization 19/	t _{d(RD-VERIFY)}			All	9, 10, 11	10		μS	
Flash EEPROM - Prog	gramming opera	ation (maximum programm	ning temperature	85°C for	flash memor	y)			
Pulse duration, programming algorithm 19/	t _{w(PGM)}			All	9, 10, 11	95	105	μs	
Delay time, program mode select to stabilization 19/	t _{d(PGM-MODE)}			All	9, 10, 11	10		μS	
Flash EEPROM – Eras	se operation					L	•		
Pulse duration, erase algorithm 19/	t _{w(ERASE)}			All	9, 10, 11	6.65	7.35	ms	
Delay time, erase mode select to stabilization 19/	td(ERASE-MODE)			All	9, 10, 11	10		μS	
Flash EEPROM – Flash	-write operation	<u>. </u>						<u> </u>	
Pulse duration, flash-write algorithm 19/ 20/	t _{w(FLW)}			All	9, 10, 11	13.3	14.7	ms	
Delay time, flash- write mode select to stabilization 19/ 20/	t _d (FLW-MODE)			All	9, 10, 11	10		μs	
JTAG timings	Į.								
TMS/TDI setup to TCK high	t _{su}	See figure 5		All	9, 10, 11	20		ns	
TMS/TDI hold from TCK high	t _h			All	9, 10, 11	15		ns	
TCK low to TDO valid	t _d			All	9, 10, 11		30	ns	
See footnotes on next s	sheet.								
	STANDARD		SIZE A				5962-9	8612	
MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990				REVIS	ION LEVEL F		SHEET 21		

TABLE I. Electrical performance characteristics - Continued.

- 1/ Not production tested.
- 2/ This device utilizes a fully static design and, therefore, can operate with input clock cycle time [tc(Cl)] approaching infinity. The device is characterized at frequencies approaching 0 Hz.
- 3/ Timing assumes CLKOUT is set to output CPUCLK. CLKOUT is initialized to CPUCLK by power-on reset.
- 4/ SYSCLK is initialized to divide-by-4 mode by any device reset.
- 5/ All timings with respect to CLKOUT/IOPC1 assume CLKSRC[1:0] bits are set to select CPUCLK for output.
- 6/ The READY timings are based on one software wait state. At full speed operation, the device does not allow for single READY-based wait states.
- $\overline{2}$ / The parameter $t_{w(RSL1)}$ refers to the time \overline{RS} is an output.
- 8/ The parameter $t_{w(RSL)}$ refers to the time RS is an input.
- 9/ This is the minimum time the MP/MC pin needs to be stable in order to be recognized by internal logic; however, for proper operation, the user must maintain a valid level for the duration of the entire memory access (or accesses) on- or off-chip.
- $\underline{10}$ / t_c = system clock cycle time = 1/SYSCLK = t_{c(SYS)}.
- 11/ The MASTER/SLAVE bit (SPICTL.2) is set and the CLOCK PHASE bit (SPICTL.3) is cleared.
- 12/ The active edge of the SPICLK signal referenced is controlled by the CLOCK POLARITY bit (SPICCR.6).
- 13/ The MASTER/SLAVE bit (SPICTL.2) is set and the CLOCK PHASE bit (SPICTL.3) is set.
- 14/ The MASTER/SLAVE bit (SPICTL.2) is cleared and the CLOCK PHASE bit (SPICTL.3) is cleared.
- 15/ The MASTER/SLAVE bit (SPICTL.2) is cleared and the CLOCK PHASE bit (SPICTL.3) is set.
- 16/ Absolute resolution = 4.89 mV. At V_{REFHI} = 5 V and V_{REFLO} = 0 V, this is one LSB. As V_{REFHI} decreases, V_{REFLO} increases, or both, the LSB sizes decrease. Therefore, the absolute accuracy and differential/integral linearity errors in terms of LSBs increase.
- 17/ The total sample/hold and conversion time is determined by the summation of td(SOC-SH), tw(SH), tw(C), and td(EOC-FIFO).
- 18/ Start of conversion is signaled by the ADCIMSTART bit or the ADCSOC bit set in software, the external start signal active (ADCSOC), or internal EVSOC signal active.
- 19/ These parameters are used in the flash programming algorithms.
- <u>20</u>/ Refer to the recommended operating conditions section for the flash programming operating temperature range when programming flash.

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Dimensions									
Symbol	Millime	Millimeters		Inches		Millim	neters	In	ches
	Min	Max	Min	Max		Min	Max	Min	Max
Α	2.79	3.81	.110	.150	D2/E2	37.08	39.12	1.460	1.540
b	0.20	0.36	.008	.014	D3/E3	20.32	2 TYP	.80) TYP
С	0.10	0.20	.004	.008	е	0.635	BSC	.02	5 BSC
D1/E1	23.75	24.51	.935	.965					

FIGURE 1. Case outline.

STANDARD	SIZE
MICROCIRCUIT DRAWING	A
DLA LAND AND MARITIME	
COLUMBUS, OHIO 43218-3990	

SIZE A		5962-98612
	REVISION LEVEL F	SHEET 23

Case outline X						
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol	
1	WE	23	D10	45	SPISIMO/IO	
2	DV_{DD}	24	D11	46	Vss	
3	Vss	25	D12	47	DV_{DD}	
4	R/\overline{W}	26	D13	48	SPISOMI/IO	
5	BR	27	D14	49	SPICLK/IO	
6	STRB	28	D15	50	V _{CCP} /WDDIS	
7	CV_DD	29	Vss	51	SPISTE/IO	
8	CVss	30	TCK	52	PDPINT	
9	D0	31	TDI	53	XINT1	
10	D1	32	TRST	54	XINT2/IO	
11	D2	33	TMS	55	XINT3/IO	
12	D3	34	TDO	56	OSCBYP	
13	DV _{DD}	35	RS	57	XTAL2	
14	Vss	36	READY	58	XTAL1/CLKIN	
15	D4	37	MP/ MC	59	Vss	
16	D5	38	EMU0	60	CV_DD	
17	D6	39	EMU1/OFF	61	Vss	
18	D7	40	NMI	62	DV _{DD}	
19	D8	41	PORESET	63	ADCSOC/IOPC0	
20	Vss	42	RESERVED	64	CLKOUT/IOPC1	
21	DV _{DD}	43	SCIRXD/IO	65	XF/IOPC2	
22	D9	44	SCITXD/IO	66	BIO /IOPC3	

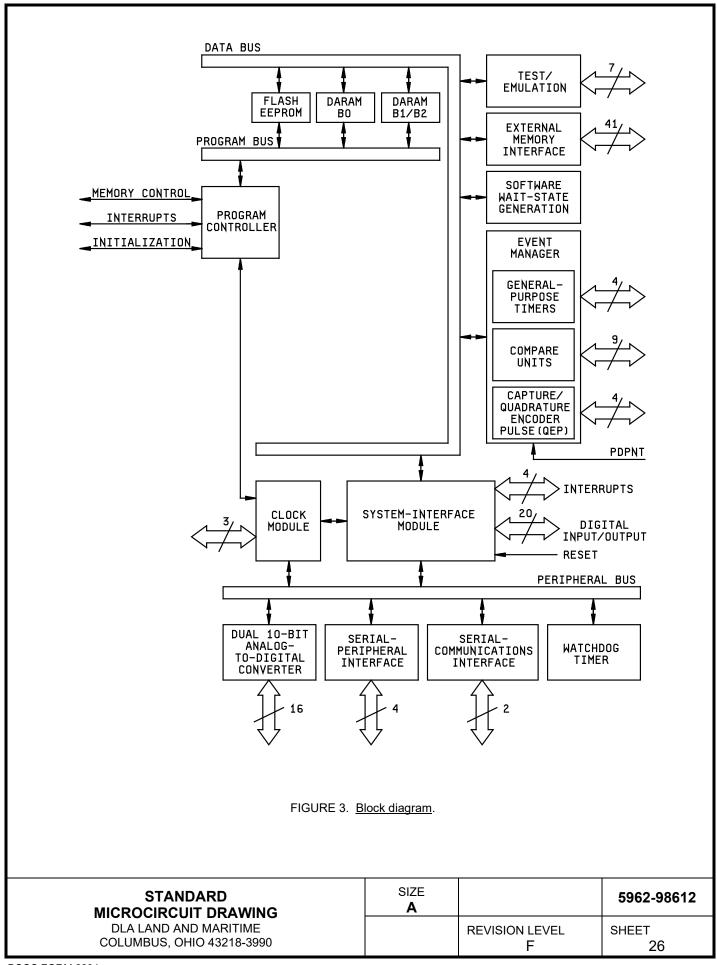
FIGURE 2. <u>Terminal connections</u>.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		F	24

	Case outline X						
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol		
67	CAP1/QEP1/IOPC4	89	ADCIN10	111	A1		
68	CAP2/QEP2/IOPC5	90	ADCIN9/IOPA2	112	A2		
69	CAP3/IOPC6	91	ADCIN8/IOPA3	113	Vss		
70	CAP4/IOPC7	92	Vss	114	А3		
71	Vss	93	DV _{DD}	115	A4		
72	ADCIN0/IOPA0	94	PWM1/CMP1	116	A5		
73	ADCIN1/IOPA1	95	PWM2/CMP2	117	A6		
74	ADCIN2	96	PWM3/CMP3	118	A7		
75	ADCIN3	97	PWM4/CMP4	119	A8		
76	ADCIN4	98	PWM5/CMP5	120	Vss		
77	ADCIN5	99	PWM6/CMP6	121	DV_{DD}		
78	ADCIN6	100	PWM7/CMP7/IOPB0	122	A9		
79	ADCIN7	101	PWM8/CMP8/IOPB1	123	A10		
80	ADCIN15	102	PWM9/CMP9/IOPB2	124	A11		
81	ADCIN14	103	DV _{DD}	125	A12		
82	ADCIN13	104	V _{SS}	126	A13		
83	ADCIN12	105	T1PWM/T1CMP/IOPB3	127	A14		
84	Vcca	106	T2PWM/T2CMP/IOPB4	128	A15		
85	V_{REFHI}	107	T3PWM/T3CMP/IOPB5	129	DS		
86	Vreflo	108	TMRDIR/IOPB6	130	ĪS		
87	Vssa	109	TMRCLK/IOPB7	131	PS		
88	ADCIN11	110	A0	132	W/R		

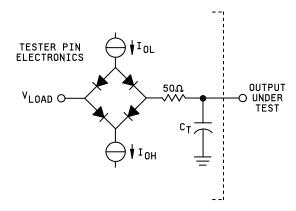
FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		F	25



Instruction code	Instruction name
00000000	EXTEST
11111111	BYPASS
00000010	SAMPLE
00000110	TRIBYP
00000011	INTEST

FIGURE 4. Boundary scan instruction codes.



NOTES:

 I_{OL} = 2 mA (all outputs) I_{OH} = 300 μ A (all outputs)

 $V_{LOAD} = 1.5 \dot{V}$

C_T = 110-pF typical load-circuit capacitance

TEST LOAD CIRCUIT

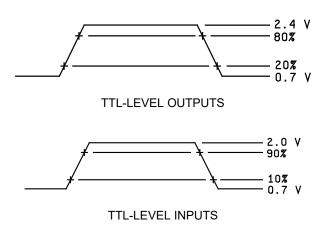
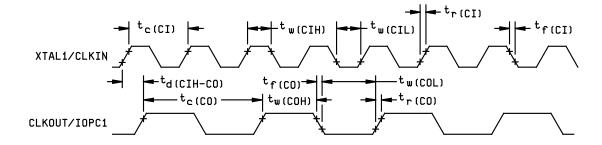
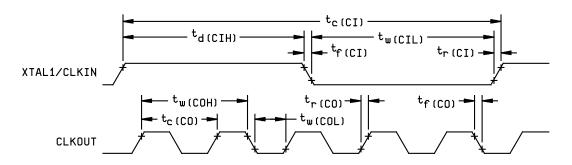


FIGURE 5. Test circuit and timing waveforms.

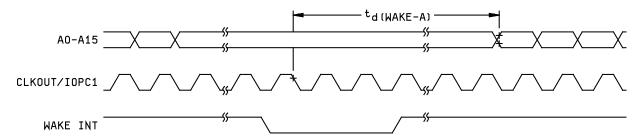
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		F	27



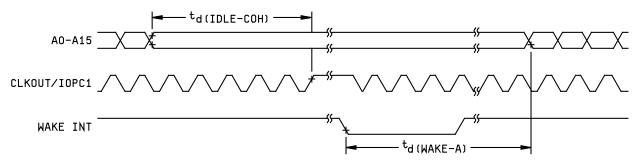
EXTERNAL DIVIDE-BY-TWO CLOCK TIMINGS



CLKIN-TO-CLKOUT TIMINGS FOR PLL OSCILLATOR MODE, MULTIPLY-BY-5 OPTION WITH 4-MHz CRYSTAL



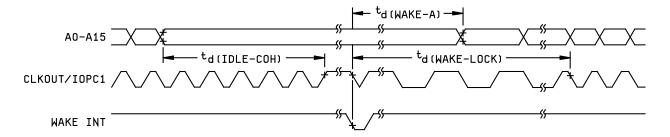
IDLE1 ENTRY AND EXIT TIMINGS



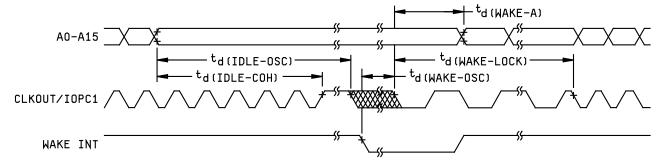
IDLE2 ENTRY AND EXIT TIMINGS

FIGURE 5. <u>Test circuit and timing waveforms</u> - Continued.

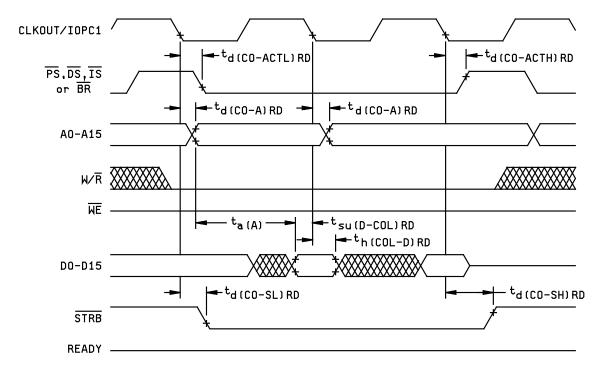
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990		REVISION LEVEL F	SHEET 28



PLL POWER-DOWN ENTRY AND EXIT TIMINGS



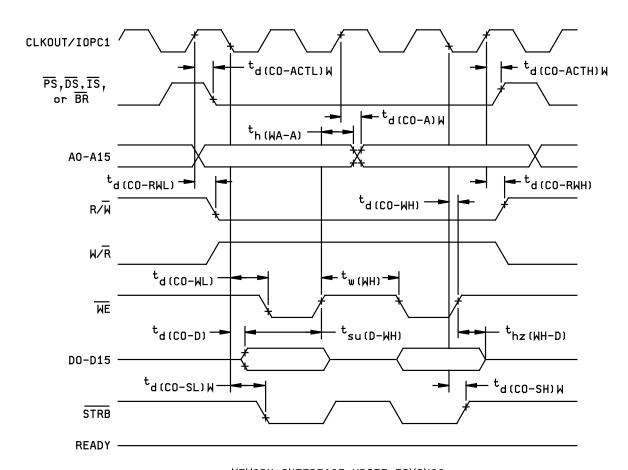
OSC POWER-DOWN ENTRY AND EXIT TIMINGS



MEMORY INTERFACE READ TIMINGS

FIGURE 5. Test circuit and timing waveforms - Continued.

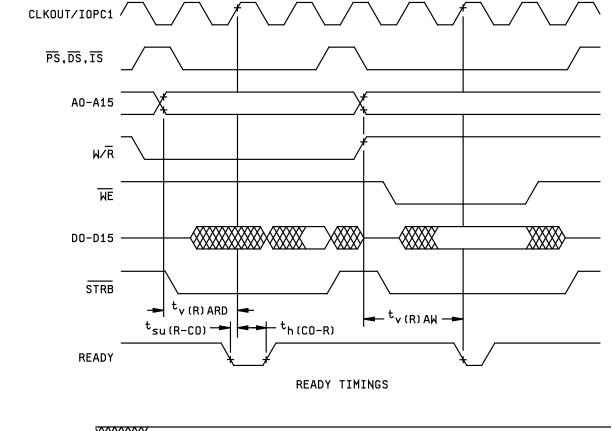
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990		REVISION LEVEL F	SHEET 29

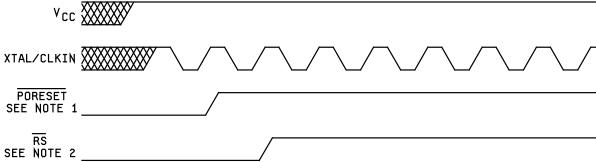


MEMORY INTERFACE WRITE TIMINGS

FIGURE 5. <u>Test circuit and timing waveforms</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		F	30





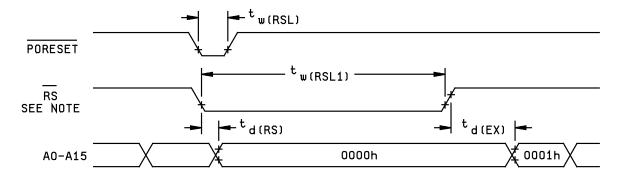
RESET TIMINGS

NOTES:

- 1. PORESET is required to be driven low during power up to ensure all clock/PLL registers are reset to a known state.
- 2. $\overline{\text{RS}}$ is a bidirectional (open-drain output) pin and can be optionally pulled low through an open-drain or open-collector drive circuit, or through a 2.7-k Ω resistor in series with a totem pole drive circuit. If $\overline{\text{RS}}$ is left undriven, then a 20-k Ω pullup resistor should be used.

FIGURE 5. Test circuit and timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME		REVISION LEVEL	SHEET
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POWER-ON RESET TIMINGS

NOTE: $\overline{\text{RS}}$ is driven low by any device reset, which includes asserting $\overline{\text{PORESET}}$, $\overline{\text{RS}}$, access to an illegal address, execution of a software reset, or a watchdog timer reset.

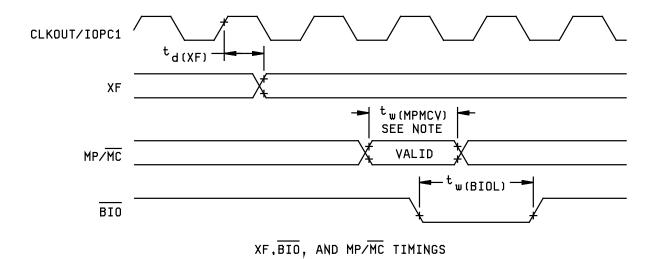
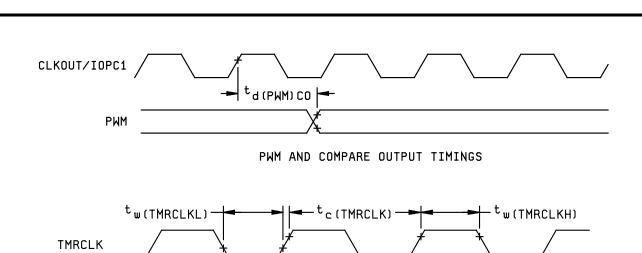


FIGURE 5. Test circuit and timing waveforms - Continued.

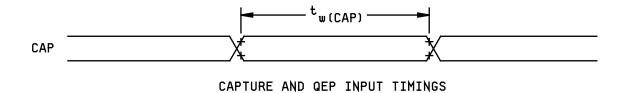
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990		REVISION LEVEL F	SHEET 32

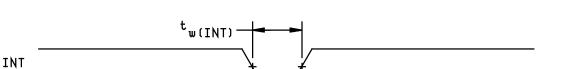


TMRDIR tw(TMRDIR)

EXTERNAL TIMER DIRECTION INPUT TIMINGS

EXTERNAL TIMER CLOCK INPUT TIMINGS

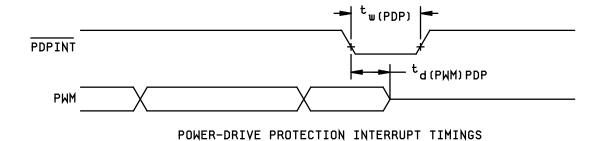




EXTERNAL INTERRUPT TIMINGS

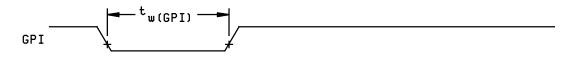
FIGURE 5. Test circuit and timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990		REVISION LEVEL F	SHEET 33



CLKOUT/IOPC1 t_d(GPO)CO

GENERAL-PURPOSE OUTPUT TIMINGS



GPO

GENERAL-PURPOSE INPUT TIMINGS

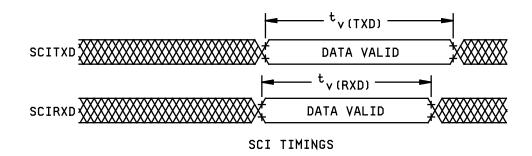
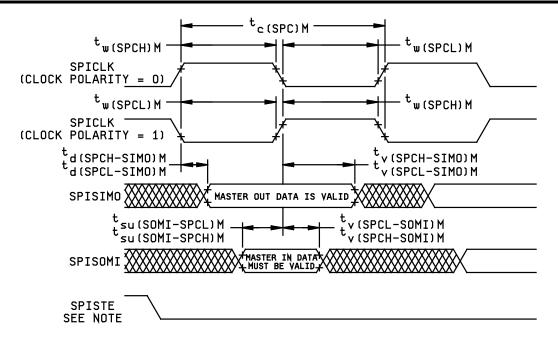
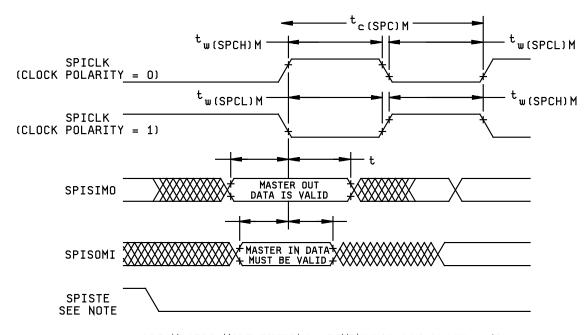


FIGURE 5. Test circuit and timing waveforms - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98612
DLA LAND AND MARITIME		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		F	34



SPI MASTER MODE EXTERNAL TIMINGS (CLOCK PHASE = 0)

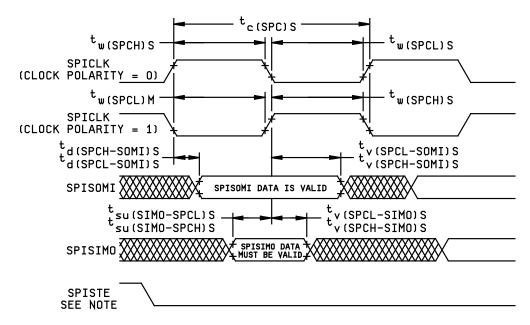


SPI MASTER MODE EXTERNAL TIMINGS(CLOCK PHASE = 1)

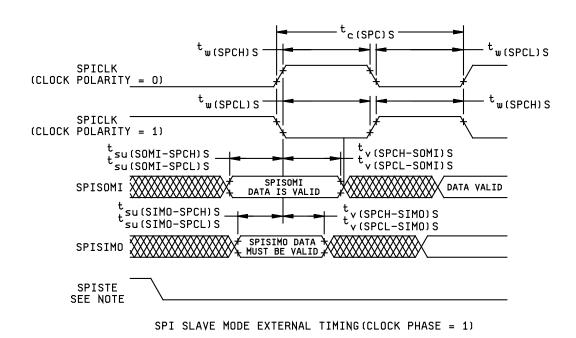
NOTE: The SPISTE signal must be active before the SPI communication stream starts; the SPISTE signal must remain active until the SPI communication stream is complete.

FIGURE 5. Test circuit and timing waveforms - Continued.

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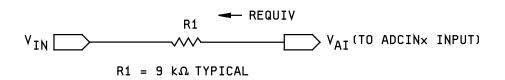
SPI SLAVE MODE EXTERNAL TIMING(CLOCK PHASE = 0)



NOTE: The SPISTE signal must be active before the SPI communication stream starts; the SPISTE signal must remain active until the SPI communication stream is complete.

FIGURE 5. Test circuit and timing waveforms - Continued.

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TYPICAL ADC INPUT PIN CIRCUIT

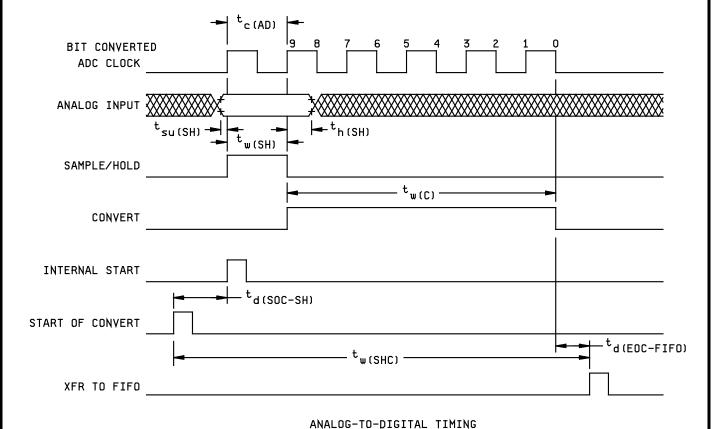
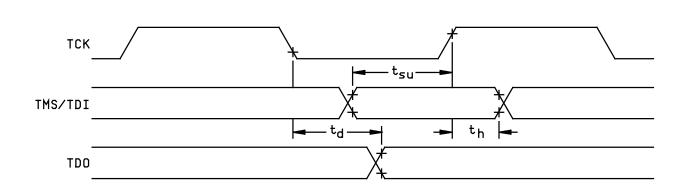


FIGURE 5. Test circuit and timing waveforms - Continued.

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JTAG TIMING

FIGURE 5. <u>Test circuit and timing waveforms</u> - Continued.

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4. VERIFICATION

- 4.1 <u>Sampling and inspection</u>. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 4.2 <u>Screening</u>. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.
 - 4.2.1 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.
- 4.3 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein.
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.
 - c. Subgroup 4 (C_I and C_O measurements) shall be measured only for initial test and after process or design changes which may affect input and output capacitance. A minimum sample size of 5 devices with zero rejects shall be required.
 - 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table II herein.
- 4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
 - 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

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TABLE II. Electrical test requirements.

Test requirements	(in accor	groups dance with 8535, table III)
	Device class Q	Device class V
Interim electrical parameters (see 4.2)		1
Final electrical parameters (see 4.2)	1, 2, 3, 7, 8, 9, 10, 11 <u>1</u> /	1, 2, 3, 7, 8, 9, 10, 11 <u>2</u> /
Group A test requirements (see 4.4)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9
Group D end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9

^{1/} PDA applies to subgroup 1.

- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C \pm 5°C, after exposure, to the subgroups specified in table II herein.

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^{2/} PDA applies to subgroups 1 and 7.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal, or email communication.
- 6.3 <u>Record of users</u>. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime -VA, telephone (614) 692-8108.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DLA Land and Maritime -VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0591.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and table III herein.
 - 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime -VA and have agreed to this drawing.

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TABLE III. Terminal descriptions.

Terminal name	Type <u>1</u> /	Description		
EXTERNAL INTERFACE DATA/ADDRESS SIGNALS				
A0 through A15	O/Z	Parallel address bus A0 [least significant bit (LSB)] through A15 [most significant bit (MSB)]. A15-A0 are multiplexed to address external data/program memory or I/O. A15-A0 are placed in the high-impedance state when EMU1/ OFF is active low and hold their previous states in power-down modes.		
D0 through D15	I/O/Z	Parallel data bus D0 (LSB) through D15 (MSB). D15-D0 are multiplexed to transfer data between the device and external data/program memory and I/O space (devices). D15-D0 are placed in the high-impedance state when not outputting, when in power-down mode, when reset		
		(RS) is asserted, or when EMU1/OFF is active low.		
	Т	EXTERNAL INTERFACE CONTROL SIGNALS		
DS, PS, IS	O/Z	Data, program, and I/O space select signals. \overline{DS} , \overline{PS} , and \overline{IS} are always high unless low-level asserted for communication to a particular external space. They are placed in the high-impedance state during reset, power down, and when EMU1/ \overline{OFF} is active low.		
READY	I	Data ready. READY indicates that an external device is prepared for the bus transaction to be completed. If the device is not ready (READY is low), the processor waits one cycle and checks READY again.		
R/W	O/Z	Read/write signal. R/ W indicates transfer direction during communication to an external device. It is normally in read mode (high), unless low level is asserted for performing a write operation. It is placed in the high-impedance state during reset, power down, and when EMU1/OFF is active low.		
STRB	O/Z	Strobe. STRB is always high unless asserted low to indicate an external bus cycle. It is placed in the high-impedance state during reset, power down, and when EMU1/OFF is active low.		
WE	O/Z	Write enable. The falling edge of WE indicates that the device is driving the external data bus (D15-D0). Data can be latched by an external device on the rising edge of WE. WE is active on all external program, data, and I/O writes. WE goes in the high-impedance state following reset and when EMU1/OFF is active low.		
W/R	O/Z	Write/read. W/\overline{R} is an inverted form of R/\overline{W} and can connect directly to the output enable of external devices. W/\overline{R} is placed in the high-impedance state following reset and when EMU1/ \overline{OFF} is active low.		
BR	O/Z	Bus request. \overline{BR} is asserted during access of external global data memory space. \overline{BR} can be used to extend the data memory address space by up to 32K words. \overline{BR} goes in the high-impedance state during reset, power down, and when EMU1/ \overline{OFF} is active low.		
Vccp/WDDIS	I	Flash-programming voltage supply. If $V_{\text{CCP}} = 5 \text{ V}$, then WRITE/ERASE can be made to the ENTIRE on-chip flash memory block - that is, for programming the flash. If $V_{\text{CCP}} = 0 \text{ V}$, then WRITE/ERASE of the flash memory is not allowed, thereby protecting the entire memory block from being overwritten. WDDIS also functions as a hardware watchdog disable. The watchdog timer is disabled when $V_{\text{CCP}}/\text{WDDIS} = 5 \text{ V}$ and bit 6 in WDCR is set to 1.		

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TABLE III. <u>Terminal descriptions</u> – Continued.

Terminal name	Type <u>1</u> /	Description		
ADC INPUTS (UNSHARED)				
ADCIN2 through ADCIN7	I	Analog inputs to the first ADC.		
ADCIN10 through ADCIN15	I	Analog inputs to the second ADC		
		BIT I/O AND SHARED FUNCTIONS PINS		
ADCIN0/IOPA0	I/O	Bidirectional digital I/O. Analog input to the first ADC. ADCIN0/IOPA0 is configured as a digital input by all device resets.		
ADCIN1/IOPA1	I/O	Bidirectional digital I/O. Analog input to the first ADC. ADCIN1/IOPA1 is configured as a digital input by all device resets.		
ADCIN9/IOPA2	I/O	Bidirectional digital I/O. Analog input to the second ADC. ADCIN9/IOPA2 is configured as a digital input by all device resets.		
ADCIN8/IOPA3	I/O	Bidirectional digital I/O. Analog input to the second ADC. ADCIN8/IOPA3 is configured as a digital input by all device resets.		
PWM7/CMP7/ IOPB0	I/O/Z	Bidirectional digital I/O. Simple compare/PWM 1 output. The state of PWM7/CMP7/IOPB0 is determined by the simple compare/PWM and the simple action control register (SACTR). It		
		goes to the high-impedance state when unmasked PDPINT goes active low. PWM7/CMP7/IOPB0 is configured as a digital input by all device resets.		
PWM8/CMP8/ IOPB1	I/O/Z	Bidirectional digital I/O. Simple compare/PWM 2 output. The state of PWM8/CMP8/IOPB1 is determined by the simple compare/PWM and the SACTR. It goes to the high-impedance state		
		when unmasked PDPINT goes active low. PWM8/CMP8/IOPB1 is configured as a digital input by all device resets.		
PWM9/CMP9/ IOPB2	I/O/Z	Bidirectional digital I/O. Simple compare/PWM 3 output. The state of PWM9/CMP9/IOPB2 is determined by the simple compare/PWM and the SACTR. It goes to the high-impedance state		
		when unmasked PDPINT goes active low. PWM9/CMP9/IOPB2 is configured as a digital input by all device resets.		
T1PWM/T1CMP/ IOPB3	I/O/Z	Bidirectional digital I/O. Timer 1 compare output. T1PWM/T1CMP/IOPB3 goes to the		
ЮРВЗ		high-impedance state when unmasked PDPINT goes active low. This pin is configured as a digital input by all device resets.		
T2PWM/T2CMP/	I/O/Z	Bidirectional digital I/O. Timer 2 compare output. T2PWM/T2CMP/IOPB4 goes to the		
IOPB4		high-impedance state when unmasked PDPINT goes active low. This pin is configured as a digital input by all device resets.		
T3PWM/T3CMP/	I/O/Z	Bidirectional digital I/O. Timer 3 compare output. T3PWM/T3CMP/IOPB5 goes to the		
IOPB5		high-impedance state when unmasked PDPINT goes active low. This pin is configured as a digital input by all device resets.		
TMRDIR/IOPB6	I/O	Bidirectional digital I/O. Direction signal for the timers. Up-counting direction if TMRDIR/IOPB6 is low, down-counting direction if this pin is high. This pin is configured as a digital input by all device resets.		
TMRCLK/IOPB7	I/O	Bidirectional digital I/O. External clock input for general-purpose timers. This pin is configured as a digital input by all device resets.		

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TABLE III. <u>Terminal descriptions</u> – Continued.

	1			
Terminal name	Type <u>1</u> /	Description		
	BIT I/O AND SHARED FUNCTIONS PINS – CONTINUED			
ADCSOC/IOPC0	I/O	Bidirectional digital I/O. External start of conversion input for ADC. This pin is configured as a digital input by all device resets.		
CAP1/QEP1/ IOPC4	I/O	Bidirectional digital I/O. Capture 1 or QEP 1 input. This pin is configured as a digital input by all device resets.		
CAP2/QEP2/ IOPC5	I/O	Bidirectional digital I/O. Capture 2 or QEP 2 input. This pin is configured as a digital input by all device resets.		
CAP3/IOPC6	I/O	Bidirectional digital I/O. Capture 3 input. This pin is configured as a digital input by all device resets.		
CAP4/IOPC7	I/O	Bidirectional digital I/O. Capture 4 input. This pin is configured as a digital input by all device resets.		
XF/IOPC2	I/O	Bidirectional digital I/O. External flag output (latched software-programmable signal). XF is used for signaling other processors in multiprocessing configurations or as a general-purpose output pin. This pin is configured as an external flag output by all device resets.		
BIO /IOPC3	I/O	Bidirectional digital I/O. Branch control input. $\overline{\text{BIO}}$ is polled by the BIOZ instruction. If $\overline{\text{BIO}}$ is		
		low, the CPU executes a branch. If $\overline{\text{BIO}}$ is not used, it should be pulled high. This pin is configured as a branch-control input by all device resets.		
CLKOUT/IOPC1	I/O	Bidirectional digital I/O. Clock output. Clock output is selected by the CLKSRC bits in the SYSCR register. This pin is configured as a DSP clock output by a power-on reset.		
		SERIAL COMMUNICATIONS INTERFACE (SCI) AND BIT I/O PINS		
SCITXD/IO	I/O	SCI asynchronous serial port transmit data, or general-purpose bidirectional I/O. This pin is configured as a digital input by all device resets.		
SCIRXD/IO	I/O	SCI asynchronous serial port receive data, or general-purpose bidirectional I/O. This pin is configured as a digital input by all device resets.		
		SERIAL PERIPHERAL INTERFACE (SPI) AND BIT I/O PINS		
SPISIMO/IO	I/O	SPI slave in, master out, or general-purpose bidirectional I/O. This pin is configured as a digital input by all device resets.		
SPISOMI/IO	I/O	SPI slave out, master in, or general-purpose bidirectional I/O. This pin is configured as a digital input by all device resets.		
SPICLK/IO	I/O	SPI clock, or general-purpose bidirectional I/O. This pin is configured as a digital input by all device resets.		
SPISTE/IO	I/O	SPI slave transmit enable (optional), or general-purpose bidirectional I/O. This pin is configured as a digital input by all device resets.		
COMPARE SIGNALS				
PWM1/CMP1 through PWM6/CMP6	O/Z	Compare units compare or PWM outputs. The state of these pins is determined by the compare/PWM and the full action control register (ACTR). CMP1-CMP6 go to the high-impedance state when unmasked PDPINT goes active low, and when reset (RS) is asserted.		
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TABLE III. Terminal descriptions - Continued. Terminal name Туре Description <u>1</u>/ INTERRUPT AND MISCELLANEOUS SIGNALS I/O $\overline{\mathsf{RS}}$ Reset input. \overline{RS} causes the device to terminate execution and sets PC = 0. When \overline{RS} is brought to a high level, execution begins at location zero of program memory. RS affects (or sets to zero) various registers and status bits. RS is a bidirectional (open-drain output) pin. ı MP/MC MP/ MC (microprocessor/microcomputer) select. If MP/MC is low, internal program memory is selected. If it is high, external program memory is selected. Nonmaskable interrupt. When NMI is activated, the device is interrupted regardless of the state NMI of the INTM bit of the status register. NMI has programmable polarity. PORESET Power-on reset. PORESET causes the device to terminate execution and sets PC = 0. When PORESET is brought to a high level, execution begins at location zero of program memory. PORESET affects (or sets to zero) the same registers and status bits as RS. In addition, PORESET initializes the PLL control registers. XINT1 ı External user interrupt no. 1. XINT2/IO I/O External user interrupt no. 2. General-purpose bidirectional I/O. This pin is configured as a digital input by all device resets. XINT3/IO External user interrupt no. 3. General-purpose bidirectional I/O. This pin is configured as a I/O digital input by all device resets. 1 **PDPINT** Maskable power-drive protection interrupt. If PDPINT is unmasked and it goes active low, the timer compare outputs immediately go to the high-impedance state. **CLOCK SIGNALS** XTAL2 O PLL oscillator output. XTAL2 is tied to one side of a reference crystal when the device is in PLL mode (CLKMD[1:0] = 1x, CKCR0.7-6). This pin can be left unconnected in oscillator bypass mode ($\overline{OSCBYP} \le V_{IL}$). This pin goes in the high-impedance state when EMU1/ \overline{OFF} is active low. XTAL1/CLKIN PLL oscillator input. XTAL1/CLKIN is tied to one side of a reference crystal in PLL mode I/Z (CLKMD[1:0] = 1x, CKCR0.7-6), or is connected to an external clock source in oscillator bypass mode ($\overline{OSCBYP} \leq V_{\parallel}$). Bypass oscillator if low. **OSCBYP SUPPLY SIGNALS** CVss ı Digital core logic ground reference. V_{SS} ı Digital logic ground reference. Vssa Analog ground reference. Digital I/O logic supply voltage.

See footnotes at end of table.

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Digital core logic supply voltage.

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DV_{DD} 2/

CV_{DD} 2/

TABLE III. <u>Terminal descriptions</u> – Continued.

Terminal name	inal name Type Description		
	SUPPLY SIGNALS - CONTINUED		
Vcca	1	Analog supply voltage.	
V _{REFHI}	1	ADC analog voltage reference high.	
V _{REFLO}	I	ADC analog voltage reference low.	
		TEST SIGNALS	
тск	I IEEE standard test clock. TCK is normally a free-running clock signal with The changes on test-access port (TAP) input signals (TMS and TDI) are closed controller, instruction register, or selected test data register of the device conformal of TCK. Changes at the TAP output signal (TDO) occur on the falling edge.		
TDI I IEEE standard test data input (TDI). TDI is clocked into the selected register (instruction on a rising edge of TCK.		IEEE standard test data input (TDI). TDI is clocked into the selected register (instruction or data) on a rising edge of TCK.	
TDO	O/Z	IEEE standard test data output (TDO). The contents of the selected register (instruction or data) are shifted out of TDO on the falling edge of TCK. TDO is in the high-impedance state when OFF is active low.	
TMS	I	IEEE standard test mode select. This serial control input is clocked into the TAP controller on the rising edge of TCK.	
operations of the device. If this		IEEE standard test reset. TRST, when active low, gives the scan system control of the operations of the device. If this signal is not connected or driven low, the device operates in its functional mode, and the test reset signals are ignored.	
EMU0	I/O/Z	Emulator pin 0. When TRST is driven low, EMU0 must be high for activation of the OFF condition. When TRST is driven high, EMU0 is used as an interrupt to or from the emulator system and is defined as input/output through the scan.	
EMU1/OFF	I/O/Z	Emulator pin 1/disable all outputs. When TRST is driven high, EMU1/OFF is used as an interrupt to or from the emulator system and is defined as input/output through JTAG scan. When TRST is driven low, this pin is configured as OFF. When EMU1/OFF is active low, it puts all output drivers in the high-impedance state. OFF is used exclusively for testing and emulation purposes (not for multiprocessing applications); therefore, for OFF condition, the following conditions apply: TRST = low, EMU0 = high, EMU1/OFF = low.	
RESERVED	I	Reserved for test. This pin has an internal pulldown and must be left unconnected for the device.	

- $\underline{1}$ / I = Input; O = Output; Z = High impedance.
- 2/ V_{DD} refers to supply voltage types CV_{DD} (digital core supply voltage), DV_{DD} (digital I/O supply voltage), and V_{DDP} (programming voltage supply). All voltages are measured with respect to V_{SS} .

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STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 24-05-08

Approved sources of supply for SMD 5962-98612 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at https://landandmaritimeapps.dla.mil/programs/smcr/.

	Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
	5962-9861201QXA	01295	SMJ320F240HFPM40
ſ	5962-9861202QXA	<u>3</u> /	SMJ320F240HFPW40

- The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 3/ Not available from an approved source of supply.

 Vendor CAGE
 Vendor name

 number
 and address

01295

Texas Instruments, Inc. Semiconductor Group 8505 Forest Lane P.O. Box 660199 Dallas, TX 75243

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